

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

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SD1536-08

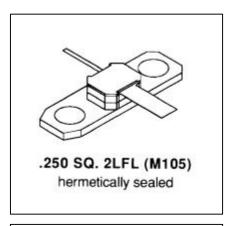
RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

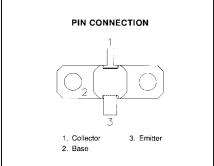
Features

- 1025 1150 MHz
- 50 VOLTS
- **P**_{OUT} = 90 **WATTS**
- G_P = 8.4 dB MINIMUM
- INPUT MATCHED
- COMMON BASE CONFIGURATION



The SD1536-08 is a gold metallized silicon NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME and TACAN. Internal Impedance matching provides improved broadband performance.





ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector – Base Voltage	65	V
V _{CES}	Collector – Emitter Voltage	65	V
V _{EBO}	Emitter – Base Voltage	3.5	V
Ic	Device Current	10	Α
P _{DISS}	Power Dissipation	292	W
T _J	Juction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{TH(J-C)}	Junction-Case Thermal Resistance	0.60	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Cymbol	Test Conditions		Value			
Syllibol	Symbol Test Conditions		Min.	Тур.	Max.	Unit
BV _{CBO}	I _C = 10 mA	I _E = 0 mA	65			V
BV _{CER}	I _C = 25 mA	R_{BE} =10 Ω	65			V
BV _{EBO}	I _E = 1 mA	I _C = 0 mA	3.5			V
I _{CES}	V _{CE} = 50 V	I _E = 0 mA			10	mA
H _{FE}	V _{CE} = 5 V	$I_C = 100 \text{ mA}$	5			

DYNAMIC

Symbol Test Conditions			Value			Unit	
Syllibol	doi lest Conditions			Min.	Тур.	Max.	Offic
P _{out}	f = 1025 - 1150MHz	P _{IN} = 13.0 W	V _{CE} = 50 V	90			W
G _P	f = 1025 - 1150MHz	P _{IN} = 13.0 W	V _{CE} = 50 V	8.4			dB

Conditions: Pulse Width = 10 μ sec Duty Cycle = 1%

IMPEDANCE DATA

FREQ	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$
960 MHz	2.8 + j7.5	6.4 – j1.3
1050 MHz	3.9 + j8.2	5.8 – j1.4
1150 MHz	4.3 + j4.3	5.0 - j0.0
1215 MHz	4.9 + j4.3	4.8 – j0.0

 $P_{IN} = 13W$ $V_{CE} = 50 V$



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PACKAGE MECHANICAL DATA

